



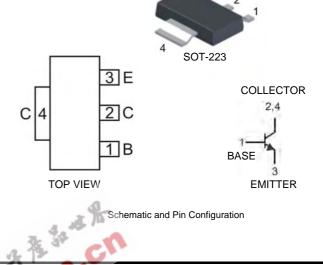
#### NPN SURFACE MOUNT TRANSISTO

#### **Features**

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DZT953)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

#### **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



#### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	I <sub>C</sub>	6	A
Power Dissipation	P <sub>tot</sub>	1 (Note 3) 3 (Note 4)	W
Operating and Storage Temperature Range	$T_{j}, T_{STG}$	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php. 2.
- Device mounted on FR-4 PCB, pad layout as shown on page 4.
- The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.

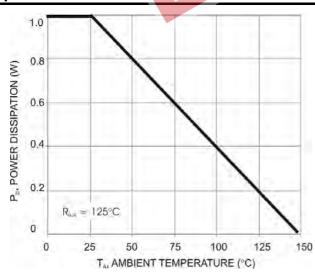


# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS									
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	200	_	_	V	$I_C = 100 \mu A, I_E = 0$			
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	100	_	_	V	$I_C = 10 \text{mA*}, I_B = 0$			
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6	_		V	$I_E = 100 \mu A, I_C = 0$			
Collector Cutoff Current	I <sub>CBO</sub>	_	_	10 1	nA μA	$V_{CB} = 150V, I_E = 0$ $V_{CB} = 150V, I_E = 0, T_A = 100$ °C			
Emitter Cutoff Current	I <sub>EBO</sub>	_		10	nA	$V_{EB} = 6V, I_{C} = 0$			
ON CHARACTERISTICS									
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>			50 150 340	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 5mA* I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA* I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA*			
Base-Emitter Saturation Voltage		_	_	1250	mV	$I_C = 5A$ , $I_B = 500mA^*$			
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	_	_	1100	mV	$I_{CE} = 5A, V_{CE} = 2V^*$			
DC Current Gain		100 100 50 20		300	_	$\begin{split} I_C &= 10 \text{mA}, \ V_{CE} = 2 \text{V}^* \\ I_C &= 2 \text{A}, \ V_{CE} = 2 \text{V}^* \\ I_C &= 4 \text{A}, \ V_{CE} = 2 \text{V}^* \\ I_C &= 10 \text{A}, \ V_{CE} = 2 \text{V}^* \end{split}$			
SMALL SIGNAL CHARACTERISTICS	SMALL SIGNAL CHARACTERISTICS								
Current Gain-Bandwidth Product		35 3	130	1-0	MHz	$I_C = 100$ mA, $V_{CE} = 10$ V, $f = 50$ MHz			
Output Capacitance	C <sub>obo</sub>		35	_	pF	$V_{CB} = 10V$ , $f = 1MHz$			
SWITCHING CHARACTERISTICS									
Switching Times	t <sub>on</sub> t <sub>off</sub>		50 1650	_	ns ns	$I_C = 1A, V_{CC} = 10V$ $I_{B1} = I_{B2} = 100mA$			

Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ 

#### Typical Characteristics @T<sub>amb</sub> = 25°C unless otherwise specified





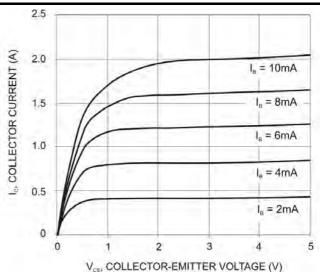


Fig. 2 Collector Current vs. Collector Emitter-Voltage

Notes: 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.



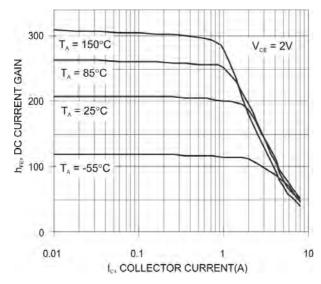


Fig. 3 Typical DC Current Gain vs. Collector Current

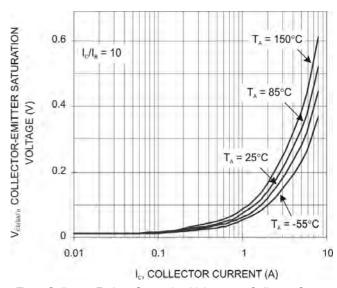


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

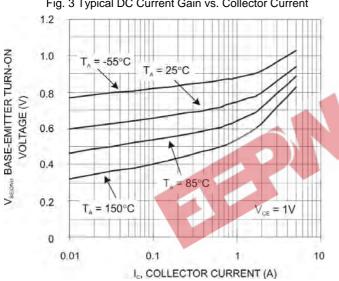


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

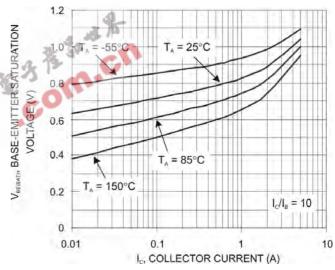


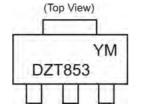
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

#### Ordering Information (Note 5)

Device	Packaging	Shipping		
DZT853-13	SOT-223	2500/Tape & Reel		

5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

#### **Marking Information**



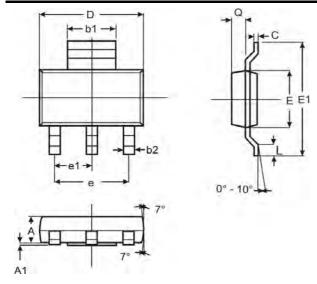
DZT853 = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Date Code Hoy												
Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

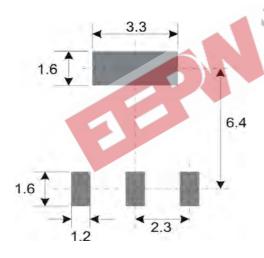


### **Package Outline Dimensions**



SOT-223							
Dim	Min	Max	Тур				
Α	1.55	1.65	1.60				
<b>A</b> 1	0.010	0.15	0.05				
b1	2.90	3.10	3.00				
b2	0.60	0.80	0.70				
С	0.20	0.30	0.25				
D	6.45	6.55	6.50				
Е	3.45	3.55	3.50				
E1	<b>E1</b> 6.90		7.00				
е	_	_	4.60				
e1	_	_	2.30				
L	0.85	1.05	0.95				
Q	0.84	0.94	0.89				
All Dimensions in mm							

## Suggested Pad Layout: (Based on IPC-SM-782)



(Unit:mm)

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